

1 1. A semiconductor structure comprising:
2 a semiconductor substrate; and
3 a Langmuir-Blodgett chemically amplified
4 photoresist formed over said semiconductor substrate.

1 2. The structure of claim 1 wherein said photoresist
2 includes a non-ionic photoacid generator.

1 3. The structure of claim 2 wherein said photoacid
2 generator is MDT.

1 4. The structure of claim 2 wherein said photoacid
2 generator is NIT.

1 5. The structure of claim 1 wherein said photoresist
2 is 193 nanometer photoresist.

1 6. The structure of claim 1 wherein said photoresist
2 is 248 nanometer photoresist.

1 7. A method comprising:
2 forming a Langmuir-Blodgett chemically amplified
3 photoresist over a semiconductor substrate.

1 8. The method of claim 7 including a non-ionic
2 photoacid generator in said photoresist.

1 9. The method of claim 8 including MDT as said
2 photoacid generator.

1 10. The method of claim 8 including NIT as said
2 photoacid generator.

1 11. The method of claim 7 including forming a 193
2 nanometer photoresist.

1 12. The method of claim 7 including forming a 248
2 nanometer photoresist.

1 13. A semiconductor structure comprising:
2 a semiconductor substrate; and
3 a Langmuir-Blodgett chemically amplified
4 photoresist over said substrate, said chemically amplified
5 photoresist including a non-ionic photoacid generator and
6 an acid sensitive polymer.

1 14. The structure of claim 13 wherein said photoacid
2 generator is MDT.

1 15. The structure of claim 13 wherein said photoacid
2 generator is NIT.